Abstract of Disclosure

SEMICONDUCTOR DEVICE WITH MINI SONOS CELL AND METHOD FOR FABRICATING THE SAME

A semiconductor device with mini silicon-oxide-nitride-oxide-silicon (mini-SONOS) cell is disclosed. The semiconductor device includes: a semiconductor substrate; a shallow trench isolation (STI) embedded in the semiconductor substrate; a logic device partially overlapping the STI; and a SONOS cell formed in the overlapped region of the logic device and the STI.

Figure 9